

# ABR600 - ABR610

**PRV : 50 - 1000 Volts**

**I<sub>o</sub> : 6.0 Amperes**

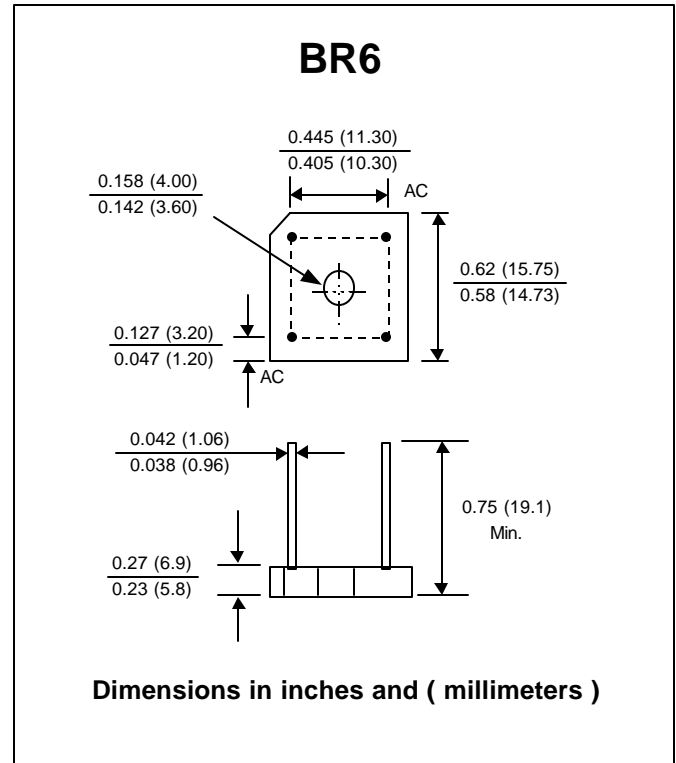
## FEATURES :

- \* High case dielectric strength
- \* High surge current capability
- \* High reliability
- \* Low reverse current
- \* Low forward voltage drop
- \* Ideal for printed circuit board

## MECHANICAL DATA :

- \* Case : Reliable low cost construction utilizing molded plastic technique
- \* Epoxy : UL94V-O rate flame retardant
- \* Lead : Axial lead solderable per MIL - STD 202 , Method 208 guaranteed
- \* Polarity : Polarity symbols marked on case
- \* Mounting position : Any
- \* Weight : 3.6 grams

# AVALANCHE BRIDGE RECTIFIERS



## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

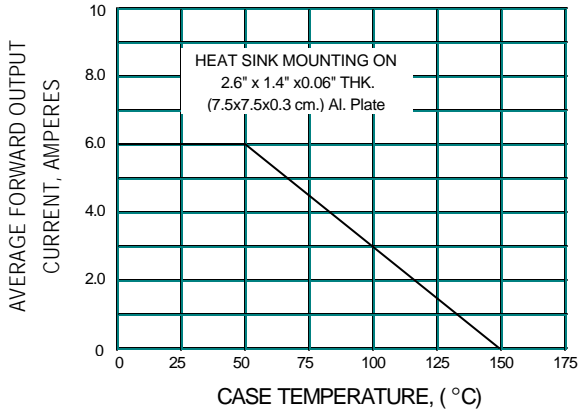
Rating at 25 °C ambient temperature unless otherwise specified.  
 Single phase, half wave, 60 Hz, resistive or inductive load.  
 For capacitive load, derate current by 20%.

RATING	SYMBOL	ABR 600	ABR 601	ABR 602	ABR 604	ABR 606	ABR 608	ABR 610	UNITS
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	50	100	200	400	600	800	1000	Volts
Maximum RMS Voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage	V <sub>DC</sub>	50	100	200	400	600	800	1000	Volts
Minimum Avalanche Breakdown Voltage at 100 μA	V <sub>BO(min.)</sub>	100	150	250	450	700	900	1100	Volts
Maximum Avalanche Breakdown Voltage at 100 μA	V <sub>BO(max.)</sub>	550	600	700	900	1150	1350	1550	Volts
Maximum Average Forward Current T <sub>c</sub> = 50°C	I <sub>F(AV)</sub>	6.0							Amps.
Peak Forward Surge Current Single half sine wave Superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	200							Amps.
Rating for fusing at ( t < 8.3 ms. )	I <sup>2</sup> t	64							A <sup>2</sup> S
Maximum Forward Voltage per Diode at I <sub>F</sub> = 3.0 Amperes.	V <sub>F</sub>	1.0							Volts
Maximum DC Reverse Current      T <sub>a</sub> = 25 °C at Rated DC Blocking Voltage      T <sub>a</sub> = 100 °C	I <sub>R</sub>	10							μA
	I <sub>R(H)</sub>	200							μA
Typical Thermal Resistance (Note 1)	R <sub>θJC</sub>	8.0							°C/W
Operating Junction Temperature Range	T <sub>J</sub>	- 50 to + 150							°C
Storage Temperature Range	T <sub>STG</sub>	- 50 to + 150							°C

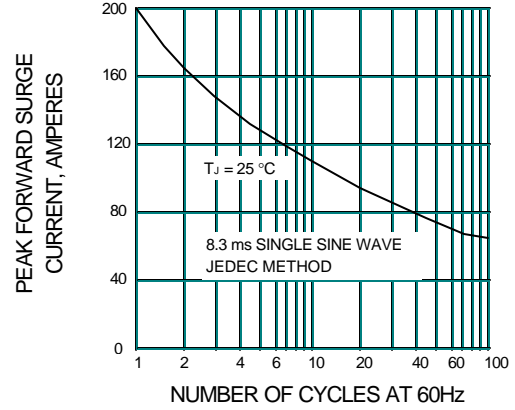
**Notes :** 1 ) Thermal resistance from Junction to case with units mounted on a 2.6" x 1.4" x 0.06" THK ( 6.5 x 3.5 x 0.15 cm ) Al. plate.

## RATING AND CHARACTERISTIC CURVES ( ABR600 - ABR610 )

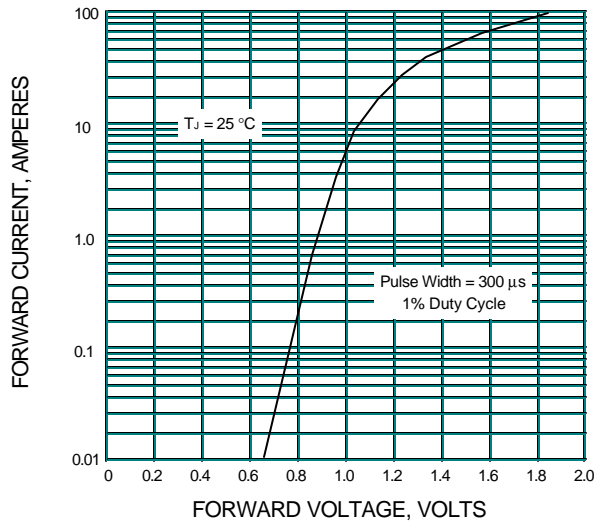
**FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT**



**FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT**



**FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE**



**FIG.4 - TYPICAL REVERSE CHARACTERISTICS**

